

BSS123LT1

Preferred Device

Power MOSFET 170 mAmps, 100 Volts

N-Channel SOT-23

Features

- Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	Vdc
Gate-Source Voltage	V_{GS}	± 20	Vdc
– Continuous	V_{GSM}	± 40	Vpk
– Non-repetitive ($t_p \leq 50 \mu s$)			
Drain Current	I_D	0.17	Adc
– Continuous (Note 1)	I_{DM}	0.68	
– Pulsed (Note 2)			

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 3) $T_A = 25^\circ C$ Derate above $25^\circ C$	P_D	225 1.8	mW mW/ $^\circ C$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ C/W$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ C$

- The Power Dissipation of the package may result in a lower continuous drain current.
- Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2.0\%$.
- FR-5 = $1.0 \times 0.75 \times 0.062$ in.



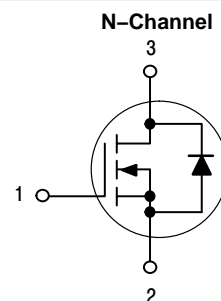
ON Semiconductor®

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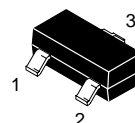
170 mAmps

100 Volts

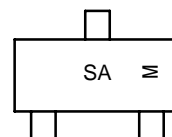
$R_{DS(on)} = 6 \Omega$



MARKING DIAGRAM

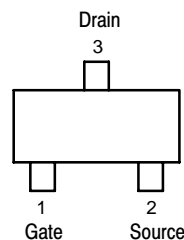


SOT-23
CASE 318
STYLE 21



SA = Device Code
M = Date Code

PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

BSS123LT1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain–Source Breakdown Voltage (V _{GS} = 0, I _D = 250 µA _{dc})	V _{(BR)DSS}	100	–	–	V _{dc}
Zero Gate Voltage Drain Current (V _{GS} = 0, V _{DS} = 100 V _{dc}) T _J = 25°C T _J = 125°C	I _{DSS}	– –	– –	15 60	µA _{dc}
Gate–Body Leakage Current (V _{GS} = 20 V _{dc} , V _{DS} = 0)	I _{GSS}	–	–	50	nA _{dc}

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 1.0 mA _{dc})	V _{GS(th)}	0.8	–	2.8	V _{dc}
Static Drain–Source On–Resistance (V _{GS} = 10 V _{dc} , I _D = 100 mA _{dc})	r _{DS(on)}	–	5.0	6.0	Ω
Forward Transconductance (V _{DS} = 25 V _{dc} , I _D = 100 mA _{dc})	g _{fs}	80	–	–	mmhos

DYNAMIC CHARACTERISTICS

Input Capacitance (V _{DS} = 25 V _{dc} , V _{GS} = 0, f = 1.0 MHz)	C _{iss}	–	20	–	pF
Output Capacitance (V _{DS} = 25 V _{dc} , V _{GS} = 0, f = 1.0 MHz)	C _{oss}	–	9.0	–	pF
Reverse Transfer Capacitance (V _{DS} = 25 V _{dc} , V _{GS} = 0, f = 1.0 MHz)	C _{rss}	–	4.0	–	pF

SWITCHING CHARACTERISTICS⁽⁴⁾

Turn–On Delay Time	(V _{CC} = 30 V _{dc} , I _C = 0.28 A _{dc} , V _{GS} = 10 V _{dc} , R _{GS} = 50 Ω)	t _{d(on)}	–	20	–	ns
Turn–Off Delay Time		t _{d(off)}	–	40	–	ns

REVERSE DIODE

Diode Forward On–Voltage (I _D = 0.34 A _{dc} , V _{GS} = 0 V _{dc})	V _{SD}	–	–	1.3	V
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4. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
BSS123LT1	SOT–23	3,000 Tape & Reel
BSS123LT1G	SOT–23 (Pb–Free)	3,000 Tape & Reel
BSS123LT3	SOT–23	10,000 Tape & Reel
BSS123LT3G	SOT–23 (Pb–Free)	10,000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL ELECTRICAL CHARACTERISTICS

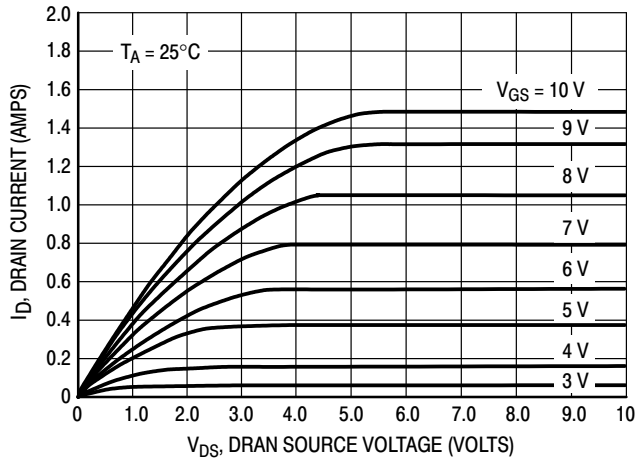


Figure 1. Ohmic Region

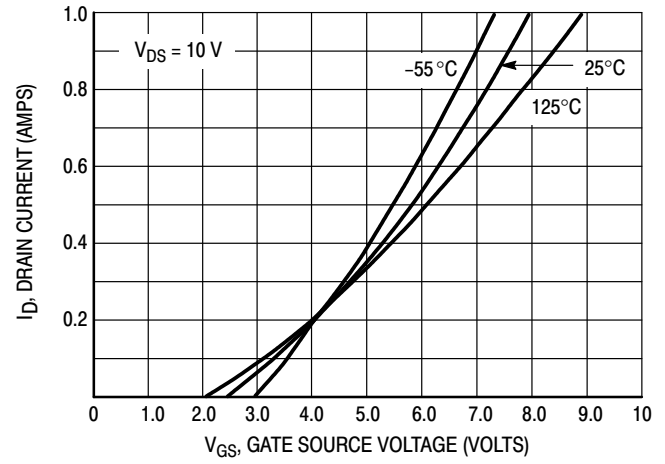


Figure 2. Transfer Characteristics

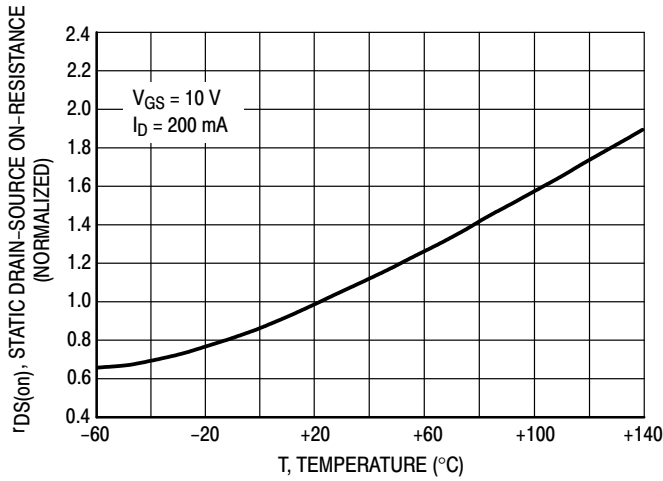


Figure 3. Temperature versus Static Drain-Source On-Resistance

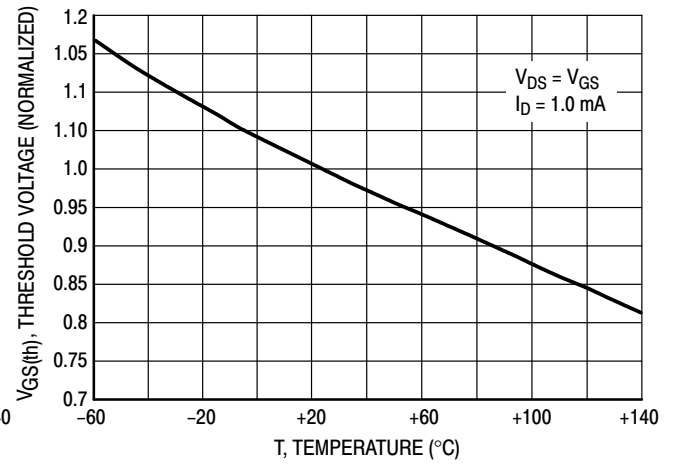
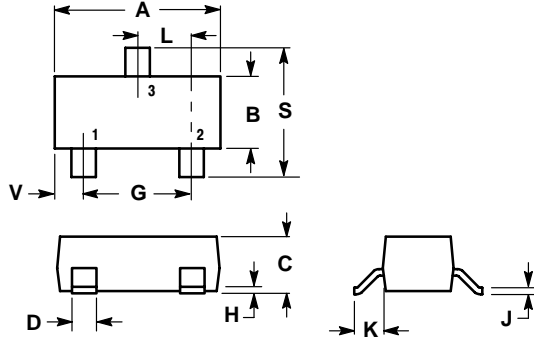


Figure 4. Temperature versus Gate Threshold Voltage

BSS123LT1

PACKAGE DIMENSIONS

SOT-23
(TO-236)
CASE 318-08
ISSUE AK



NOTES:

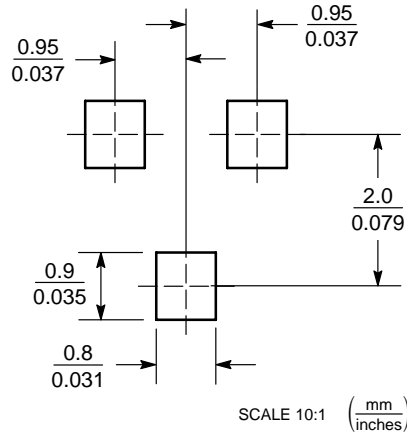
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60


STYLE 21:

- PIN 1. GATE
2. SOURCE
3. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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